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[Continued on next page]

(54) Title: THYRISTOR RANDOM ACCESS MEMORY DEVICE AND METHOD

(57) Abstract: Memory devices and methods of making memory devices are shown. Methods and configurations as shown provide folded and vertical memory devices for increased memory density. Methods provided reduce a need for manufacturing methods such as deep dopant implants.

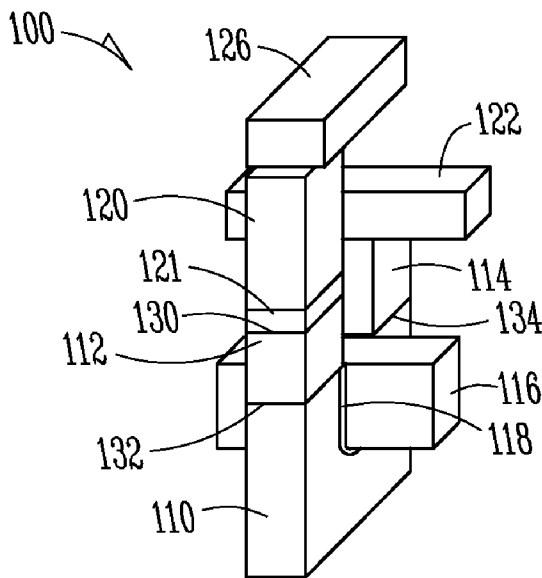


Fig. 2A



EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, **Published:**

LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK,

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